TLV2354, TLV2354Y LinCMOS™ QUADRUPLE LOW-VOLTAGE DIFFERENTIAL COMPARATORS

SLCS012C - MAY 1992 - REVISED AUGUST 2000

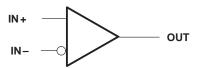
- Wide Range of Supply Voltages 2 V to 8 V
- Fully Characterized at 3 V and 5 V
- **Very-Low Supply-Current Drain** 240 μA Typ at 3 V
- Common-Mode Input Voltage Range **Includes Ground**
- High Input Impedance . . . $10^{12} \Omega$ Typ

description

The TLV2354 consists of four independent, low-power comparators specifically designed for single power-supply applications and operateS with power-supply rails as low as 2 V. When powered from a 3-V supply, the typical supply current is only 240 µA.

- Fast Response Time . . . 200 ns Typ for **TTL-Level Input Step**
- **Extremely Low Input Bias Current** 5 pA Typ
- Output Compatible With TTL, MOS, and **CMOS**
- **Built-In ESD Protection**

symbol (each comparator)



The TLV2354 is designed using the Texas Instruments LinCMOS™ technology and, therefore, features an extremely high input impedance (typically greater than $10^{12} \Omega$), which allows direct interfacing with high-impedance sources. The outputs are N-channel open-drain configurations that require an external pullup resistor to provide a positive output voltage swing, and they can be connected to achieve positive-logic wired-AND relationships. The TLV2354I is fully characterized for operation from – 40°C to 85°C. The TLV2354M is fully characterized for operation from – 55°C to 125°C.

The TLV2354 has internal electrostatic-discharge (ESD)-protection circuits and has been classified with a 1000-V ESD rating using human body model testing. However, care should be exercised in handling this device as exposure to ESD may result in degradation of the device parametric performance.

AVAILABLE OPTIONS

				PACKAGE	D DEVICES			CLUD
TA	V _{IO} max at 25°C	SMALL OUTLINE (D) [†]	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)‡	CERAMIC FLATPACK (W)	CHIP FORM (Y)
-40°C to 85°C	5 mV	TLV2354ID	_	_	TLV2354IN	TLV2354IPW	_	TLV2354Y
−55°C to 125°C	5 mV	_	TLV2354MFK	TLV2354MJ	_	_	TLV2354MW	11123341

[†] The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLV2352IDR).

[‡]The PW packages are only available left-ended taped and reeled (e.g., TLV2354IPW).



These devices have limited built-in protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



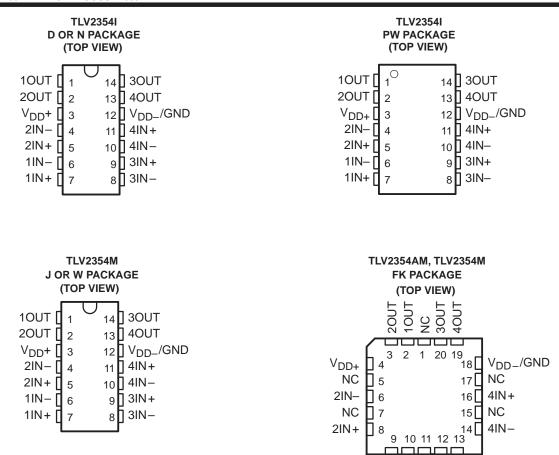
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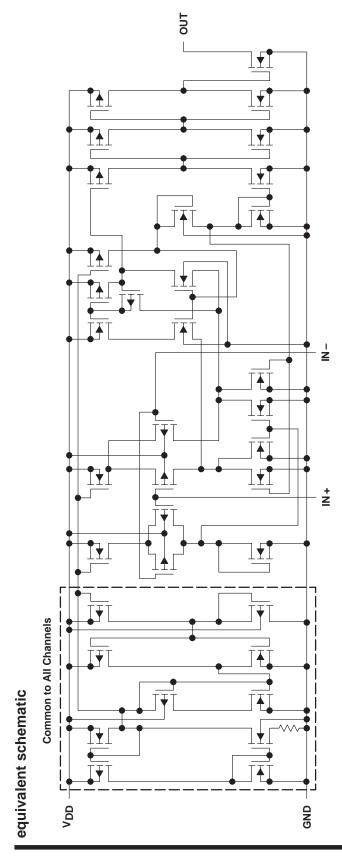
TLV2354, TLV2354Y LinCMOS™ QUADRUPLE LOW-VOLTAGE DIFFERENTIAL COMPARATORS

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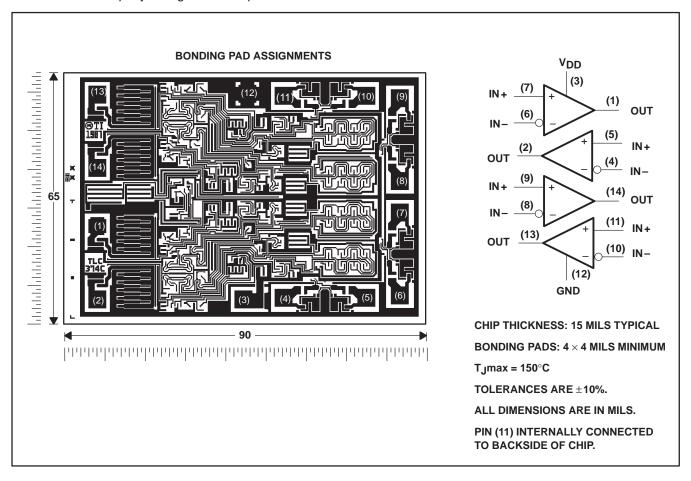
NC - No internal connection

3R-



TLV2354Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2354. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	8 V
Differential input voltage, V _{ID} (see Note 2)	±8 V
Input voltage range, V _I	0.3 to 8 V
Output voltage, VO	8 V
Input current, I _I	±5 mA
Output current, IO	20 mA
Duration of output short-circuit current to GND (see Note 3)	unlimited
Continuous total power dissipation	. See Dissipation Rating Table
Operating free-air temperature range, T _A : TLV2354I	40°C to 85°C
TLV2354M	55°C to 125°C
Storage temperature range	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, N, or PW	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: FK, J, or W	package 300°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.

- 2. Differential voltages are at the noninverting input terminal with respect to the inverting input terminal.
- 3. Short circuits from outputs to $V_{\mbox{DD}}$ can cause excessive heating and eventual device destruction.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	950 mW	7.6 mW/°C	494 mW	_
FK	1375 mW	11.0 mW/°C	715 mW	275 mW
J	1375 mW	11.0 mW/°C	715 mW	275 mW
N	1150 mW	9.2 mW/°C	598 mW	_
PW	700 mW	5.6 mW/°C	364 mW	_
W	700 mW	5.5 mW/°C	370 mW	150 mW

recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V _{DD}		2	8	V
Common mode input voltage V.a	V _{DD} = 3 V	0	1.75	V
Common-mode input voltage, V _{IC}	V _{DD} = 5 V	0	3.75	V
Operating free-air temperature, T _A	TLV2354I	-40	85	°C
Coperating need an temperature, 14	TLV2354M	-55	125	

electrical characteristics at specified free-air temperature

							TLV2	23541			
	PARAMETER	TEST CON	DITIONS	T _A ‡	V	DD = 3 \	1	VI	_{DD} = 5 V	'	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V/10	Input offset voltage	Vio - Vionmin	See Note 4	25°C		1	5		1	5	mV
VIO	input onset voitage	$V_{IC} = V_{ICRmin}$	3ee 110te 4	Full range			7			7	IIIV
li o	Input offset current			25°C		1			1		pА
ΙΟ	input onset current			85°C			1			1	nA
	Input bias current			25°C		5			5		pА
ΙΒ	input bias current			85°C			2			2	nA
	Common-mode input			25°C	0 to 2			0 to 4			
VICR	voltage range			Full range	0 to 1.75			0 to 3.75			V
1	High-level output	V 4 V		25°C		0.1			0.1		nA
ЮН	current	V _{ID} = 1 V		Full range			1			1	μΑ
V	Low-level output	V 4 V	Ja. 2 m A	25°C		115	300		150	400	mA
VOL	voltage	$V_{ID} = -1 V$,	$I_{OL} = 2 \text{ mA}$	Full range			600			700	ША
lOL	Low-level output current	V _{ID} = −1 V,	V _{OL} = 1.5 V	25°C	6	16		6	16		mA
	Cupply ourrant	V:= - 1 V	No load	25°C		240	500		290	600	
IDD	Supply current	V _{ID} = 1 V,	NO IOAU	Full range			700			800	μΑ

[†] All characteristics are measured with zero common-mode input voltage unless otherwise noted.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V with VDD = 5 V, 2 V with VDD = 3 V, or below 400 mV with a 10-k Ω resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, V_{DD} = 3 V, T_A = 25°C

PARAMETER		Т	UNIT				
PARAMETER		TEST C	ONDITIONS	MIN	TYP	MAX	UNII
Response time	$R_L = 5.1 \text{ k}\Omega$, See Note 5	$C_L = 15 pF$,	100-mV input step with 5-mV overdrive		640		ns

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses VO = 1 V with $V_{DD} = 3 \text{ V}$ or when the output crosses $V_{O} = 1.4 \text{ with } V_{DD} = 5 \text{ V}$.

switching characteristics, $V_{DD} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER		TEST C	Т	UNIT			
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT		
Bospones time	Response time $ \begin{array}{c} R_L = 5.1 \text{ k}\Omega, \\ \text{See Note 5} \end{array} \begin{array}{c} C_L = 15 \text{ pF\$}, \\ \hline \text{TTL-level input step} \end{array} $		100-mV input step with 5-mV overdrive		650		no
Response time				200		ns	

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses VO = 1 V with V_{DD} = 3 V or when the output crosses V_{O} = 1.4 with V_{DD} = 5 V.



[‡]Full range is -40°C to 85°C. IMPORTANT: See Parameter Measurement Information.

electrical characteristics at specified free-air temperature†

							TLV2	354M			
	PARAMETER	TEST CON	DITIONS	T _A ‡	V	_{DD} = 3 V	1	V	_{DD} = 5 V	'	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V. 0	Input offset voltage	Via – Vianmin	See Note 4	25°C		1	5		1	5	mV
VIO	input onset voitage	$V_{IC} = V_{ICR}min,$	See Note 4	Full range			10			10	IIIV
lio.	Input offset current			25°C		1			1		pА
110	input onset current			125°C			10			10	nA
l.p	Input bias current			25°C		5			5		pА
IB	input bias current			125°C			20			20	nA
	Common-mode input			25°C	0 to 2			0 to 4			
VICR	voltage range			Full range	0 to 1.75			0 to 3.75			V
lau	High-level output	V:= - 1 V		25°C		0.1			0.1		nA
ЮН	current	V _{ID} = 1 V		Full range			1			1	μΑ
V/0.	Low-level output	V _{ID} = −1 V,	lα. – 2 mΔ	25°C		115	300		150	400	mA
VOL	voltage	$V_{ID} = -1 V$	$I_{OL} = 2 \text{ mA}$	Full range			600			700	IIIA
lOL	Low-level output current	V _{ID} = −1 V,	V _{OL} = 1.5 V	25°C	6	16		6	16		mA
Inn	Supply current	V:p = 1 V	No load	25°C		240	500		290	600	
IDD	Supply current	$V_{ID} = 1 V$,	INU IUAU	Full range			700			800	μΑ

TAII characteristics are measured with zero common-mode input voltage unless otherwise noted.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V with V_{DD} = 5 V, 2 V with V_{DD} = 3 V, or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, V_{DD} = 3 V, T_A = 25°C

PARAMETER		TL	UNIT				
PARAMETER		TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
Response time	R _L = 5.1 kΩ, See Note 5	C _L = 100 pF§,	100-mV input step with 5-mV overdrive			1400	ns

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses $V_O = 1 \text{ V}$ with $V_{DD} = 3 \text{ V}$ or when the output crosses $V_O = 1.4$ with $V_{DD} = 5 \text{ V}$.

switching characteristics, $V_{DD} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER		TL	UNIT				
PARAMETER		1231 0	CONDITIONS	MIN	TYP	MAX	UNIT
Response time	$R_L = 5.1 \text{ k}\Omega$,	C _L = 100 pF§,	100-mV input step with 5-mV overdrive			1300	no
Response time	See Note 5	_ ,	TTL-level input step			900	ns

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses $V_0 = 1 \text{ V}$ with $V_{DD} = 3 \text{ V}$ or when the output crosses $V_0 = 1.4$ with $V_{DD} = 5 \text{ V}$.



[‡] Full range is -55°C to 125°C. IMPORTANT: See Parameter Measurement Information.

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electrical characteristics at specified free-air temperature, $T_A = 25^{\circ}C^{\dagger}$

						TLV2	354Y			
	PARAMETER	TEST CONDITIONS		V _{DD} = 3 V			V _{DD} = 5 V			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
VIO	Input offset voltage	$V_{IC} = V_{ICR}min,$	See Note 4		1	5		1	5	mV
lio	Input offset current				1			1		pA
I _{IB}	Input bias current				5			5		pA
VICR	Common-mode input voltage range			0 to 2			0 to 4			V
IOH	High-level output current	V _{ID} = 1 V			0.1			0.1		nA
VOL	Low-level output voltage	$V_{ID} = -1 V$,	$I_{OL} = 2 \text{ mA}$		115	300		150	400	mV
loL	Low-level output current	$V_{ID} = -1 V$,	V _{OL} = 1.5 V	6	16		6	16		mA
I_{DD}	Supply current	V _{ID} = 1 V,	No load		240	500		290	600	μΑ

[†] All characteristics are measured with zero common-mode input voltage unless otherwise noted.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V with V_{DD} = 5 V, 2 V with V_{DD} = 3 V, or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.



TYPICAL CHARACTERISTICS

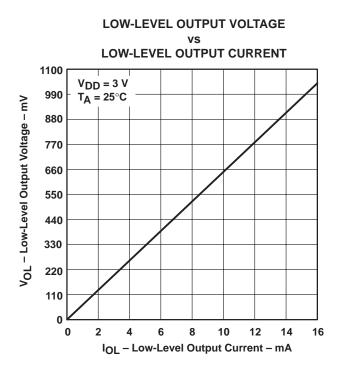


Figure 1

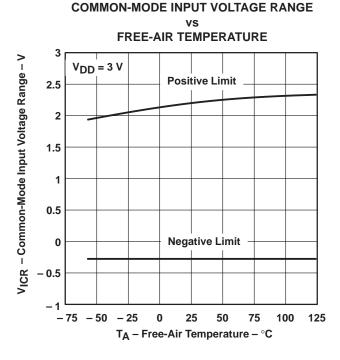


Figure 3

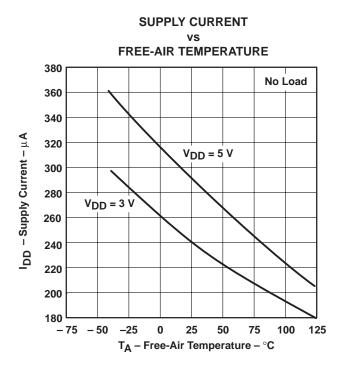


Figure 2

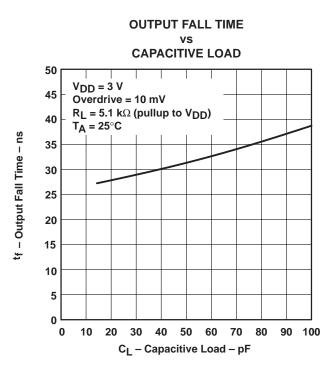


Figure 4

TYPICAL CHARACTERISTICS

HIGH-TO-LOW-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS OVERDRIVE VOLTAGES

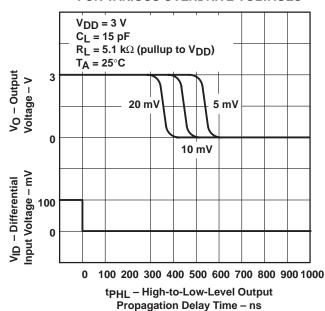


Figure 5

LOW-TO-HIGH-LEVEL OUTPUT PROPAGATION DELAY

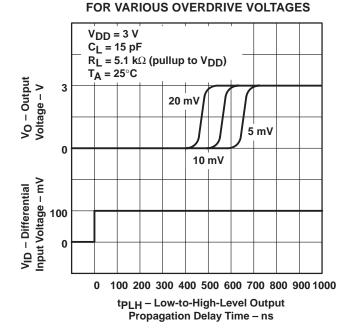


Figure 7

HIGH-TO-LOW-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS CAPACITIVE LOADS

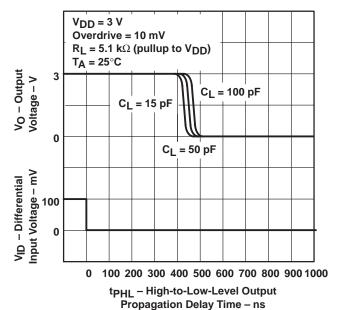


Figure 6

LOW-TO-HIGH-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS CAPACITIVE LOADS

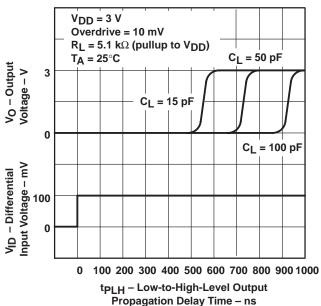


Figure 8



PARAMETER MEASUREMENT INFORMATION

The digital output stage of the TLV2354 can be damaged if it is held in the linear region of the transfer curve. Conventional operational amplifier/comparator testing incorporates the use of a servo loop that is designed to force the device output to a level within this linear region. Since the servo-loop method of testing cannot be used, the following alternatives for measuring parameters such as input offset voltage, common-mode rejection, etc., are offered.

To verify that the input offset voltage falls within the limits specified, the limit value is applied to the input as shown in Figure 9(a). With the noninverting input positive with respect to the inverting input, the output should be high. With the input polarity reversed, the output should be low.

A similar test can be made to verify the input offset voltage at the common-mode extremes. The supply voltages can be slewed as shown in Figure 9(b) for the V_{ICR} test rather than changing the input voltages to provide greater accuracy.

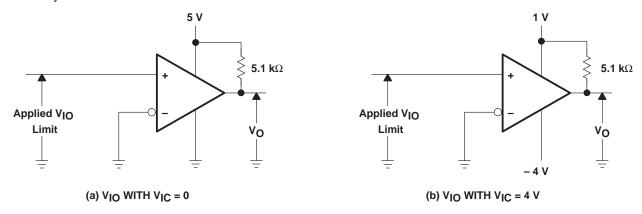


Figure 9. Method for Verifying That Input Offset Voltage Is Within Specified Limits

A close approximation of the input offset voltage can be obtained by using a binary search method to vary the differential input voltage while monitoring the output state. When the applied input voltage differential is equal but opposite in polarity to the input offset voltage, the output changes states.

PARAMETER MEASUREMENT INFORMATION

Figure 10 illustrates a practical circuit for direct dc measurement of input offset voltage that does not bias the comparator in the linear region. The circuit consists of a switching-mode servo loop in which U1a generates a triangular waveform of approximately 20-mV amplitude. U1b acts as a buffer, with C2 and R4 removing any residual dc offset. The signal is then applied to the inverting input of the comparator under test while the noninverting input is driven by the output of the integrator formed by U1c through the voltage divider formed by R9 and R10. The loop reaches a stable operating point when the output of the comparator under test has a duty cycle of exactly 50%, which can only occur when the incoming triangle wave is sliced symmetrically or when the voltage at the noninverting input exactly equals the input offset voltage.

Voltage dividers R9 and R10 provide a step up of the input offset voltage by a factor of 100 to make measurement easier. The values of R5, R8, R9, and R10 can significantly influence the accuracy of the reading; therefore, it is suggested that their tolerance level be 1% or lower.

Measuring the extremely low values of input current requires isolation from all other sources of leakage current and compensation for the leakage of the test socket and board. With a good picoammeter, the socket and board leakage can be measured with no device in the socket. Subsequently, this open-socket leakage value can be subtracted from the measurement obtained with a device in the socket to obtain the actual input current of the device.

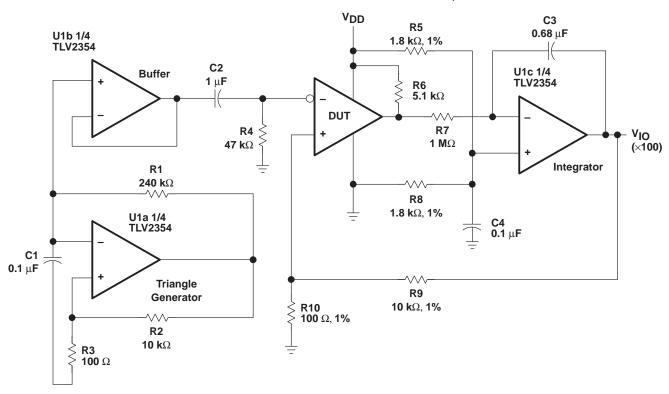
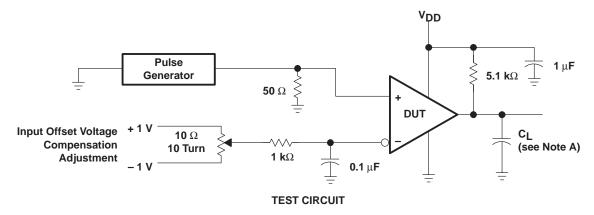


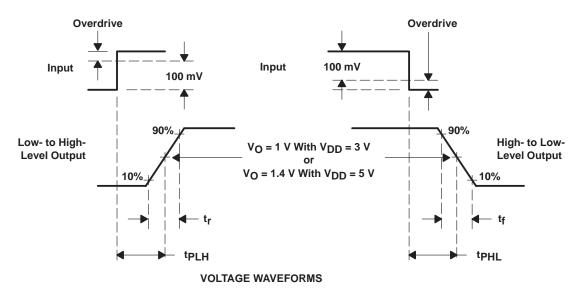
Figure 10. Circuit for Input Offset Voltage Measurement



PARAMETER MEASUREMENT INFORMATION

Propagation delay time is defined as the interval between the application of an input step function and the instant when the output crosses $V_O = 1.4 \text{ V}$ with $V_{DD} = 3 \text{ V}$ or when the output crosses $V_O = 1.4 \text{ V}$ with $V_{DD} = 5 \text{ V}$. Propagation delay time, low-to-high-level output, is measured from the leading edge of the input pulse, while propagation delay time, high-to-low-level output, is measured from the trailing edge of the input pulse. Propagation-delay-time measurement at low input signal levels can be greatly affected by the input offset voltage. The offset voltage should be balanced by the adjustment at the inverting input (as shown in Figure 11) so that the circuit is just at the transition point. Then a low signal, for example a 105-mV or 5-mV overdrive, causes the output to change state.





NOTE A: C_I includes probe and jig capacitance.

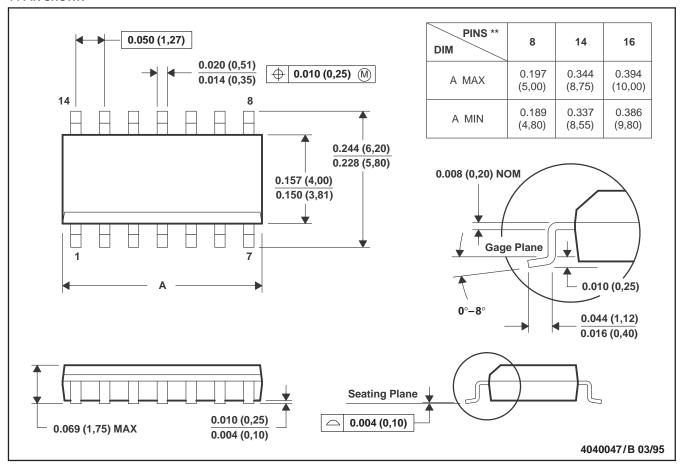
Figure 11. Propagation Delay, Rise, and Fall Times Test Circuit and Voltage Waveforms

MECHANICAL INFORMATION

D (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

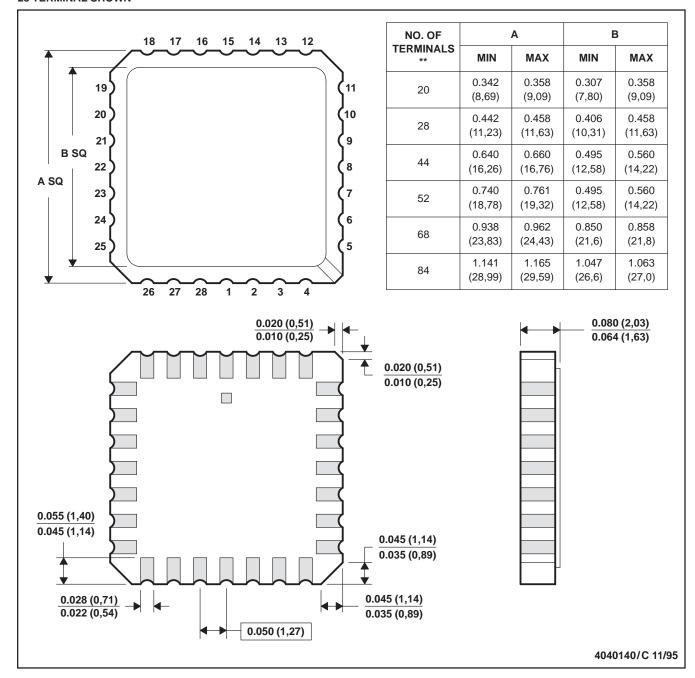
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
- D. Four center pins are connected to die mount pad.
- E. Falls within JEDEC MS-012

MECHANICAL INFORMATION

FK (S-CQCC-N**)

28 TERMINAL SHOWN

LEADLESS CERAMIC CHIP CARRIER



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. The terminals are gold plated.
- E. Falls within JEDEC MS-004



MECHANICAL INFORMATION

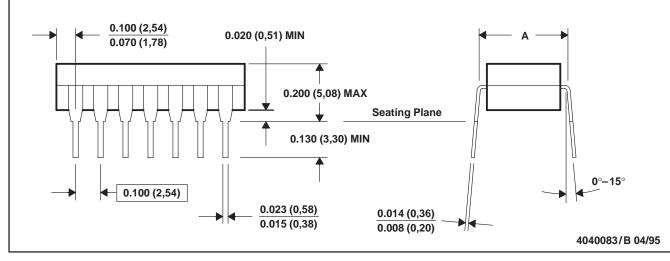
J (R-GDIP-T**) 14 PIN SHOWN

CERAMIC DUAL-IN-LINE PACKAGE

14 8 8 C

0.065 (1,65) 0.045 (1,14)

PINS **	14	16	18	20	22
A MAX	0.310	0.310	0.310	0.310	0.410
	(7,87)	(7,87)	(7,87)	(7,87)	(10,41)
A MIN	0.290	0.290	0.290	0.290	0.390
	(7,37)	(7,37)	(7,37)	(7,37)	(9,91)
B MAX	0.785	0.785	0.910	0.975	1.100
	(19,94)	(19,94)	(23,10)	(24,77)	(28,00)
B MIN	0.755 (19,18)	0.755 (19,18)		0.930 (23,62)	
C MAX	0.280	0.300	0.300	0.300	0.388
	(7,11)	(7,62)	(7,62)	(7,62)	(9,65)
C MIN	0.245 (6,22)	0.245 (6,22)	0.245 (6,22)	0.245 (6,22)	



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. This package can be hermetically sealed with a ceramic lid using glass frit.

D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.

E. Falls within MIL-STD-1835 GDIP1-T14, GDIP1-T16, GDIP1-T18, GDIP1-T20, and GDIP1-T22

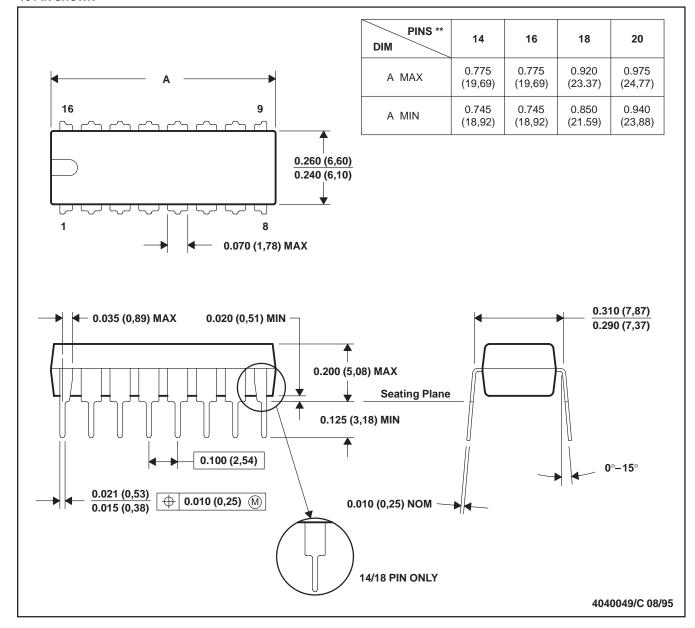


MECHANICAL INFORMATION

N (R-PDIP-T**)

16 PIN SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

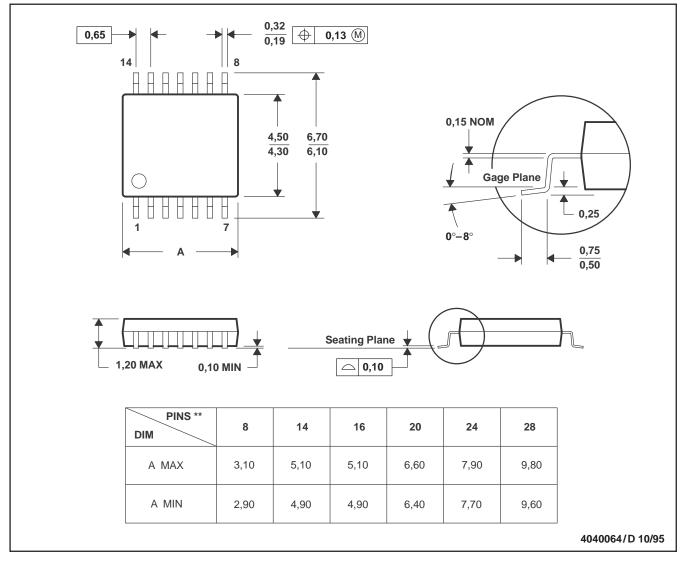
C. Falls within JEDEC MS-001 (20 pin package is shorter then MS-001.)

MECHANICAL INFORMATION

PW (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

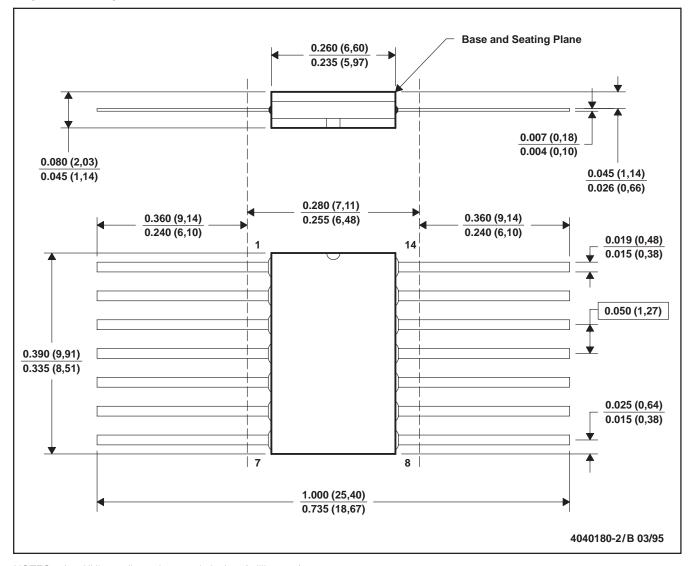
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

MECHANICAL INFORMATION

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F14 and JEDEC MO-092AB

IMPORTANT NOTICE

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